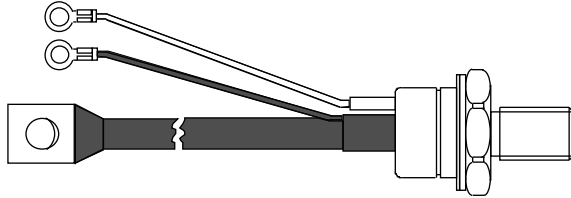


Phase Control Thyristors (Stud Version), 80 A



TO-209AC (TO-94)

FEATURES

- Hermetic glass-metal seal
- International standard case TO-209AC (TO-94)
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level



RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRODUCT SUMMARY

$I_{T(AV)}$	80 A
-------------	------

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		80	A
	T_C	85	°C
$I_{T(RMS)}$		125	A
I_{TSM}	50 Hz	1900	
	60 Hz	1990	
I^2t	50 Hz	18	kA ² s
	60 Hz	16	
V_{DRM}/V_{RRM}		400 to 1200	V
t_q	Typical	110	µs
T_J		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = 125$ °C mA
80RIA 81RIA	40	400	500	15
	80	800	900	
	120	1200	1300	

80RIA...PbF, 81RIA...PbF, 82RIA...PbF Series



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current at case temperature	$I_{T(AV)}$	180° conduction, half sine wave		80	A
				85	°C
Maximum RMS on-state current	$I_{T(RMS)}$	DC at 75 °C case temperature		125	A
Maximum peak, one-cycle non-repetitive surge current	I_{TSM}	t = 10 ms	No voltage reappplied	1900	
		t = 8.3 ms		1990	
		t = 10 ms	100 % V_{RRM} reappplied	1600	
		t = 8.3 ms		1675	
Maximum I^2t for fusing	I^2t	t = 10 ms	No voltage reappplied	18	kA ² s
		t = 8.3 ms		16	
		t = 10 ms	100 % V_{RRM} reappplied	12.7	
		t = 8.3 ms		11.7	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reappplied		180.5	kA ² /s
Low level value of threshold voltage	$V_{T(TO)1}$	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		0.99	V
High level value of threshold voltage	$V_{T(TO)2}$	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.13	
Low level value of on-state slope resistance	r_{t1}	$(16.7 \% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		2.29	mΩ
High level value of on-state slope resistance	r_{t2}	$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ maximum		1.84	
Maximum on-state voltage	V_{TM}	$I_{pk} = 250$ A, $T_J = 25$ °C, $t_p = 10$ ms sine pulse		1.60	V
Maximum holding current	I_H	$T_J = 25$ °C, anode supply 12 V resistive load		200	mA
Typical latching current	I_L			400	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	$T_J = 125$ °C, $V_d =$ Rated V_{DRM} , $I_{TM} = 2 \times$ di/dt snubber 0.2 μF, 15 Ω, gate pulse: 20 V, 65 Ω, $t_p = 6$ μs, $t_r = 0.5$ μs Per JEDEC standard RS-397, 5.2.2.6.		300	A/μs
Typical delay time	t_d	Gate pulse: 10 V, 15 Ω source, $t_p = 6$ μs, $t_r = 0.1$ μs, $V_d =$ Rated V_{DRM} , $I_{TM} = 50$ Adc, $T_J = 25$ °C		1	μs
Typical turn-off time	t_q	$I_{TM} = 50$ A, $T_J = T_J$ maximum, di/dt = - 5 A/μs, $V_R = 50$ V, dV/dt = 20 V/μs, gate bias: 0 V 25 Ω, $t_p = 500$ μs		110	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125$ °C exponential to 67 % rated V_{DRM}		500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM} , I_{DRM}	$T_J = 125$ °C rated V_{DRM}/V_{RRM} applied		15	mA



80RIA...PbF, 81RIA...PbF, 82RIA...PbF Series

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TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		12	W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$		3	
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms		3	A
Maximum peak positive gate voltage	$+V_{GM}$			20	V
Maximum peak negative gate voltage	$-V_{GM}$			10	
Maximum DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	270	mA
		$T_J = 25$ °C		120	
		$T_J = 125$ °C		60	
Maximum DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C		3.5	V
		$T_J = 25$ °C		2.5	
		$T_J = 125$ °C		1.5	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V_{DRM} anode to cathode applied	6	mA
DC gate voltage not to trigger	V_{GD}			0.25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum operating junction temperature range	T_J			- 40 to 125	°C
Maximum storage temperature range	T_{Stg}			- 40 to 150	
Maximum thermal resistance, junction to case	R_{thJC}	DC operation		0.30	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, flat and greased		0.1	
Mounting torque, ± 10 %		Non-lubricated threads		15.5 (137)	N · m (lbf · in)
		Lubricated threads		14 (120)	
Approximate weight				130	g
Case style		See dimensions - link at the end of datasheet		TO-209AC (TO-94)	

80RIA...PbF, 81RIA...PbF, 82RIA...PbF Series



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ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.042	0.030	T _J = T _J maximum	K/W
120°	0.050	0.052		
90°	0.064	0.070		
60°	0.095	0.100		
30°	0.164	0.165		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

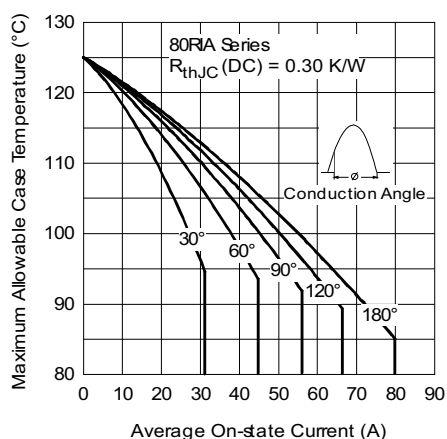


Fig. 1 - Current Ratings Characteristics

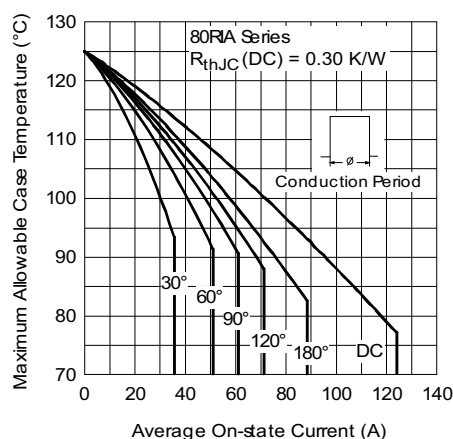


Fig. 2 - Current Ratings Characteristics

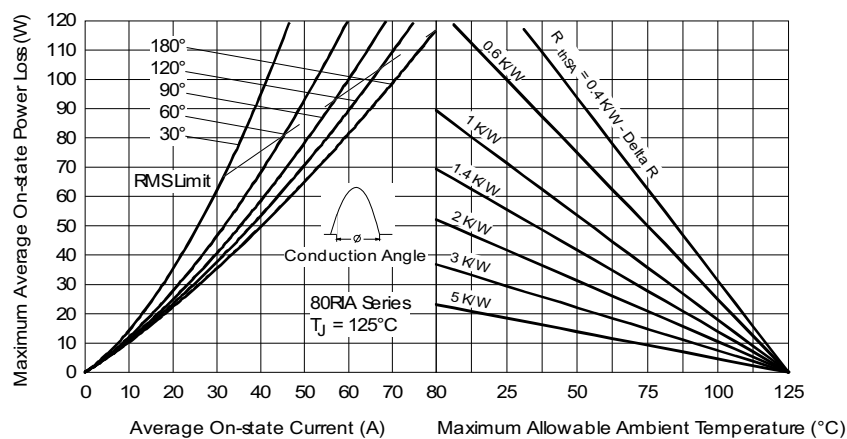


Fig. 3 - On-State Power Loss Characteristics



80RIA...PbF, 81RIA...PbF, 82RIA...PbF Series

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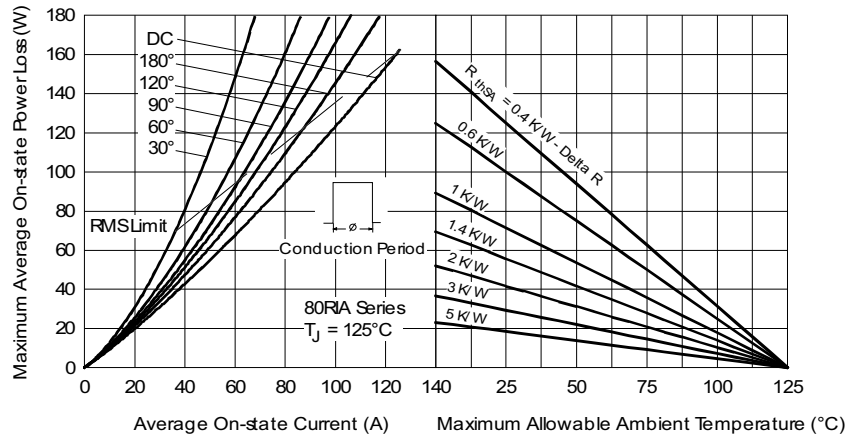


Fig. 4 - On-State Power Loss Characteristics

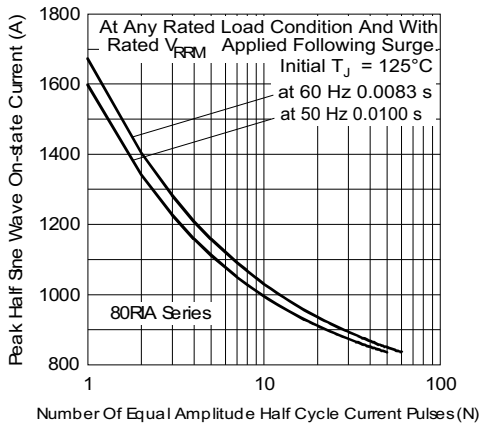


Fig. 5 - Maximum Non-Repetitive Surge Current

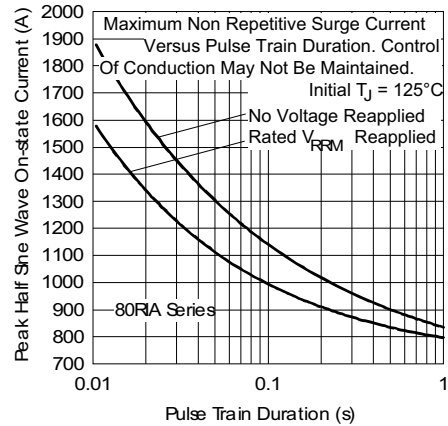


Fig. 6 - Maximum Non-Repetitive Surge Current

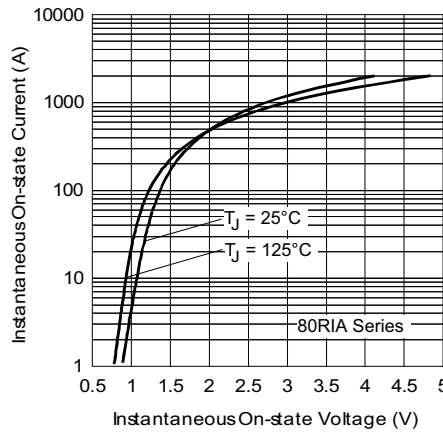


Fig. 7 - On-State Voltage Drop Characteristics

80RIA...PbF, 81RIA...PbF, 82RIA...PbF Series



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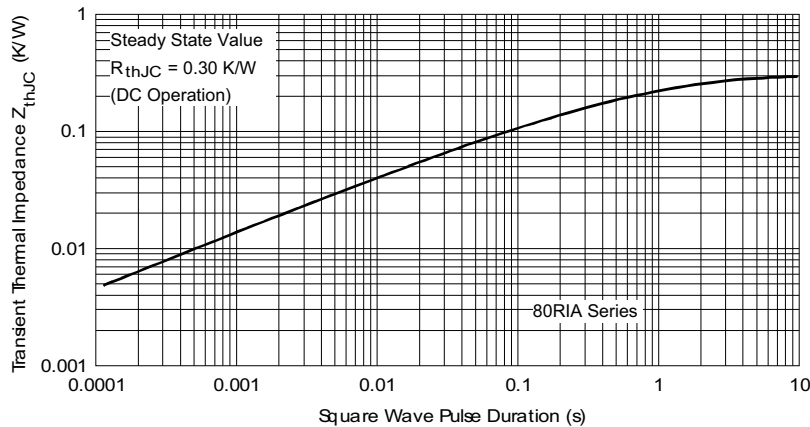


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

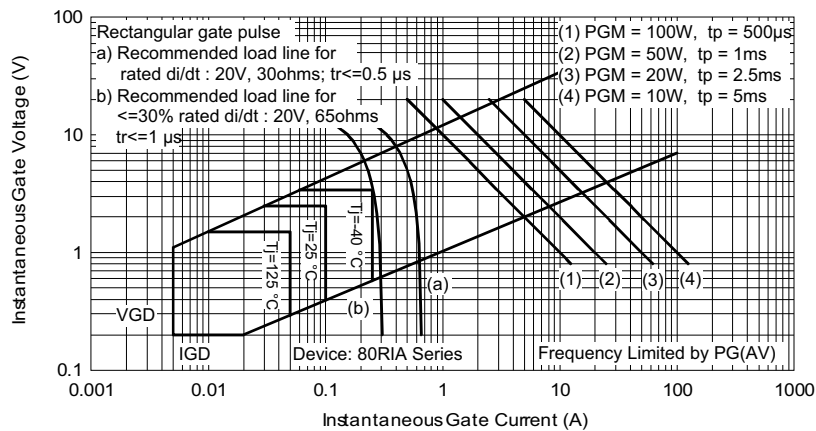


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	8	0	RIA	120	M	PbF
	(1)	(2)	(3)	(4)	(5)	(6)

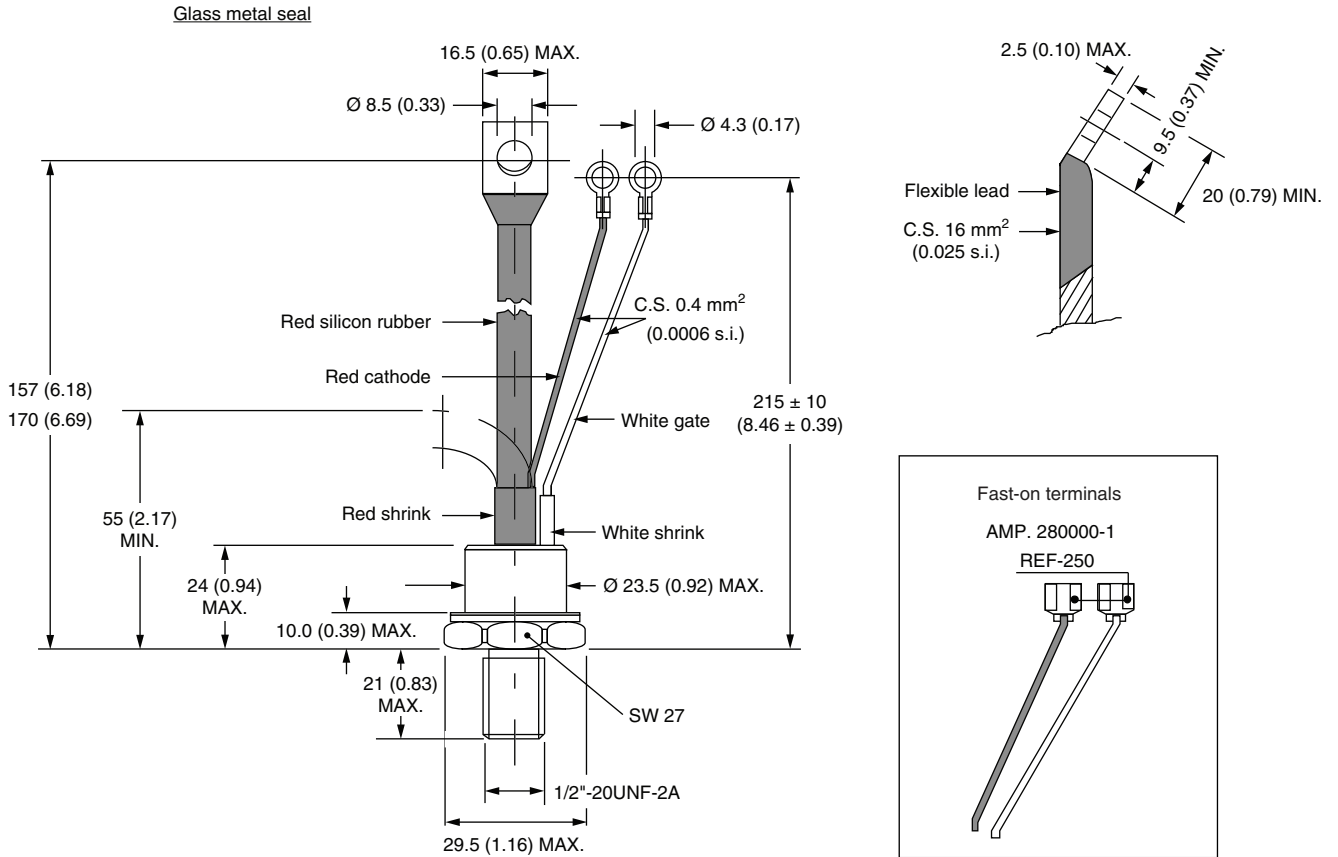
- 1** - $I_{TAV} \times 10$ A
- 2** -
 - 0 = Eyelet terminals (gate and auxiliary cathode leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode leads)
 - 2 = Flag terminals (gate and auxiliary cathode terminals)
- 3** - RIA = Essential part number
- 4** - Voltage code $\times 100 = V_{RRM}$ (see Voltage Ratings table)
- 5** -
 - None = Stud base 1/2"-20UNF- 2 A threads
 - M = Stud base metric threads M12 x 1.75 E 6
- 6** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95362
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TO-209AC (TO-94) for 80RIA Series

DIMENSIONS in millimeters (inches)





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